

TO-92MOD Plastic-Encapsulated Transistors

2SB740 TRANSISTOR (PNP)

FEATURE

Power dissipation

P_{CM} : 0.9 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -1 A

Collector-base voltage

$V_{(BR)CBO}$: -70 V

Operating and storage junction temperature range

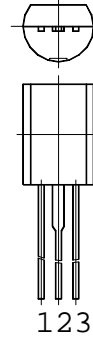
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-70		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -55V, I_E = 0$		-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$		-0.2	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -100mA$	100	320	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -1A, I_B = -100mA$		-0.6	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -10mA$	100		MHz
Output capacitance	C_{ob}	$V_{CE} = -10V, I_E = 0, f = 1MHz$		45	pF

CLASSIFICATION OF h_{FE}

Rank	B	C
Range	100-200	160-320